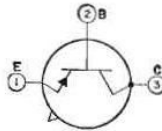


TRANSISTOR

2N966

Germanium p-n-p type used in high-speed saturated switching applications in industrial data-processing equipment. JEDEC No. TO-18 package; outline 12, Outlines Section. This type is identical with type



2N962 except for the following items:

CHARACTERISTICS

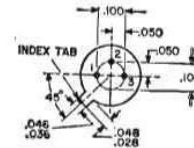
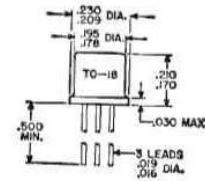
Collector-to-Emitter Saturation Voltage:

With collector ma = -10 and base ma = -1	-0.18 max	volt
With collector ma = -50 and base ma = -5	-0.35 max	volt
With collector ma = -100 and base ma = -10	-0.6 max	volt

In Common-Emitter Circuit

DC Forward Current-Transfer Ratio:

With collector-to-emitter volts = -0.3 and collector ma = -10	40 min
With collector-to-emitter volts = -1 and collector ma = -50	40 min
With collector-to-emitter volts = -1 and collector ma = -100	40 min



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<http://alltransistors.com>